# **Dual Non-Inverting Buffer, Open Drain**

The NLX2G07 MiniGate<sup>™</sup> is an advanced high–speed CMOS dual non–inverting buffer with open drain output in ultra–small footprint. The NLX2G07 input and output structures provide protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

#### **Features**

- High Speed:  $t_{PD} = 2.3 \text{ ns (Typ)} @ V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 1 \mu A \text{ (Max)}$  at  $T_A = 25^{\circ}\text{C}$
- Power Down Protection Provided on inputs
- Balanced Propagation Delays
- Overvoltage Tolerant (OVT) Input and Output Pins
- Ultra-Small Packages
- These are Pb–Free Devices

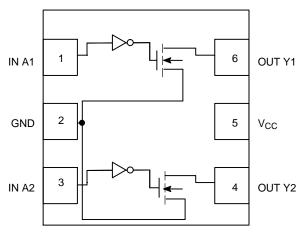


Figure 1. Pinout (Top View)

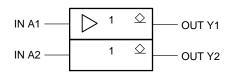


Figure 2. Logic Symbol

# PIN ASSIGNMENT

<b>FUNCTION TABLE</b>				
Α	Y			
L H	L Z			

1	IN A1
2	GND
3	IN A2
4	OUT Y2
5	V <sub>CC</sub>
6	OUT Y1



# ON Semiconductor®

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UDFN6 1.0 x 1.0 CASE 517BX





UDFN6 1.2 x 1.0 CASE 517AA





UDFN6 1.45 x 1.0 CASE 517AQ



R, A, K, V = Device Marking M = Date Code

# ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V	
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage		-0.5 to +7.0	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>IN</sub> < GND	-50	mA
l <sub>ok</sub>	DC Output Diode Current	V <sub>OUT</sub> < GND	-50	mA
I <sub>O</sub>	DC Output Source/Sink Current	±50	mA	
I <sub>CC</sub>	DC Supply Current Per Supply Pin	±100	mA	
I <sub>GND</sub>	DC Ground Current per Ground Pin	±100	mA	
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C	
TL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias	150	°C	
MSL	Moisture Sensitivity	Level 1		
F <sub>R</sub>	Flammability Rating Oxygen	Index: 28 to 34	UL 94 V-0 @ 0.125 in	
I <sub>LATCHUP</sub>	Latchup Performance Above $V_{\mbox{\footnotesize CC}}$ and Below GND at	±500	mA	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.
- Tested to EIA/JESD22-A114-A.
   Tested to EIA/UESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA / JESD78.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		1.65	5.5	V
V <sub>IN</sub>	Digital Input Voltage		0	5.5	V
V <sub>OUT</sub>	Output Voltage	0	5.5	V	
T <sub>A</sub>	Operating Free–Air Temperature		<b>-</b> 55	+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	T <sub>A</sub> = 25°C		T <sub>A</sub> = -	+85°C		55°C to 5°C		
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Low-Level Input Voltage		1.65– 1.95	0.75 x V <sub>CC</sub>			0.75 x V <sub>CC</sub>		0.75 x V <sub>CC</sub>		V
			2.3 to 5.5	0.70 x V <sub>CC</sub>			0.70 x V <sub>CC</sub>		0.70 x V <sub>CC</sub>		
V <sub>IL</sub>	Low-Level Input Voltage		1.65– 1.95			0.25 x V <sub>CC</sub>		0.25 x V <sub>CC</sub>		0.25 x V <sub>CC</sub>	V
			2.3 to 5.5			0.30 x V <sub>CC</sub>		0.30 x V <sub>CC</sub>		0.30 x V <sub>CC</sub>	
V <sub>OL</sub>	Low-Level Output	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50  \mu\text{A}$	1.65– 5.5			0.1		0.1		0.1	V
	Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \\ &I_{OL} = 12 \text{ mA} \\ &I_{OL} = 16 \text{ mA} \\ &I_{OL} = 24 \text{ mA} \\ &I_{OL} = 32 \text{ mA} \end{aligned}$	1.65 2.3 2.7 3.0 3.0 4.5		0.08 0.2 0.22 0.28 0.38 0.42	0.24 0.3 0.4 0.4 0.55 0.55		0.24 0.3 0.4 0.4 0.55 0.55		0.24 0.3 0.4 0.4 0.55 0.55	
I <sub>LKG</sub>	Z-State Output Leakage Current	$V_{IN} = V_{IH},$ $V_{OUT} = V_{CC}$ or $GND$	5.5			±5.0		±10		±10	μА
I <sub>IN</sub>	Input Leakage Current	$0 \le V_{IN} \le 5.5 V$	0 to 5.5			±0.1		±1.0		±1.0	μΑ
l <sub>OFF</sub>	Power Off Input Leakage Current	$0 \le V_{IN}, \\ V_{OUT} \le 5.5 \text{ V}$	0			1.0		10		10	μА
I <sub>CC</sub>	Quiescent Supply Current	$V_{IN} = 0$ or $V_{CC}$	5.5			1.0		10		10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ nS}$ )

	V <sub>CC</sub> Test		Test	T <sub>A</sub> = 25°C			T <sub>A</sub> = -55°C to +125°C		
Symbol	Parameter	(V)			Тур	Max	Min	Max	Unit
t <sub>PZL</sub>	Propagation Delay (Figures 3 and 4)	1.65–1.95	$R_L = R_1 = 5000 \Omega,$ $C_L = 15 pF$	1.8	5.3	11.5	1.8	12	ns
		2.3–2.7	$R_L = R_1 = 500 \Omega,$ $C_L = 50 pF$	1.2	3.7	5.8	1.2	6.4	
		3.0-3.6	$R_L = R_1 = 500 \Omega,$ $C_L = 50 pF$	0.8	2.9	4.4	0.8	4.8	
		4.5–5.5	$R_L = R_1 = 500 \Omega,$ $C_L = 50 pF$	0.5	2.3	3.5	0.5	3.9	
t <sub>PLZ</sub>	Propagation Delay (Figures 3 and 4)	1.65–1.95	$R_L = R_1 = 5000 \Omega,$ $C_L = 15 \text{ pF}$	1.8	5.3	11.5	1.8	12	ns
		2.3–2.7	$R_L = R_1 = 500 \Omega,$ $C_L = 50 \text{ pF}$	1.2	2.8	5.8	1.2	6.4	
		3.0–3.6	$R_L = R_1 = 500 \Omega,$ $C_L = 50 \text{ pF}$	0.8	2.1	4.4	0.8	4.8	
		4.5–5.5	$R_L = R_1 = 500 \Omega,$ $C_L = 50 pF$	0.5	1.4	3.5	0.5	3.9	
C <sub>IN</sub>	Input Capacitance	5.5	V <sub>IN</sub> = 0 V or V <sub>CC</sub>		2.5				pF
C <sub>OUT</sub>	Output Capacitance	5.5	V <sub>IN</sub> = 0 V or V <sub>CC</sub>		4				pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)	3.3 5.5	10 MHz V <sub>IN</sub> = 0 V or V <sub>CC</sub>		4				pF

<sup>6.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

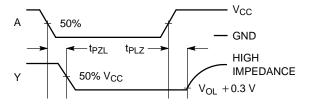
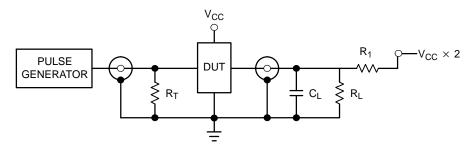


Figure 3. Switching Waveforms



 $R_T = Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )

Figure 4. Test Circuit

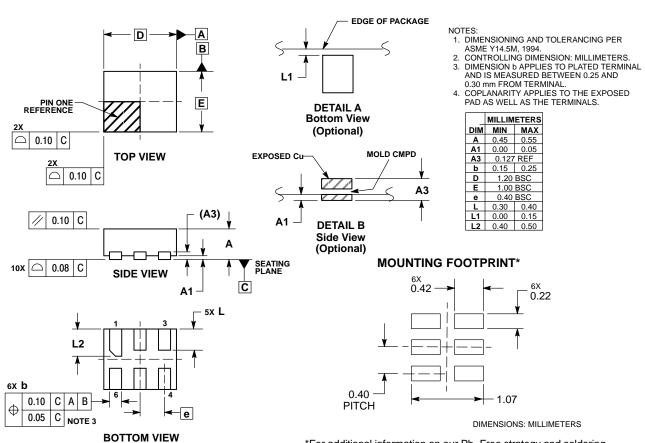
# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
NLX2G07MUTCG	UDFN6, 1.2 x 1.0, 0.4P (Pb-Free)	3000 / Tape & Reel		
NLX2G07AMUTCG	(2G07AMUTCG UDFN6, 1.45 x 1.0, 0.5P (Pb–Free)			
NLX2G07CMUTCG	UDFN6, 1.0 x 1.0, 0.35P (Pb-Free)	3000 / Tape & Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **PACKAGE DIMENSIONS**

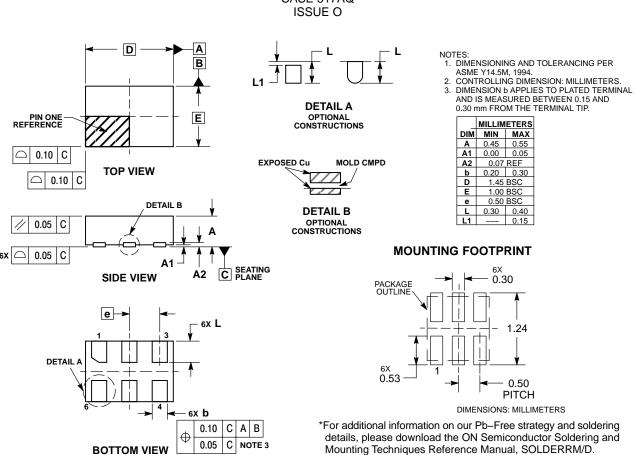
## UDFN6, 1.2x1.0, 0.4P CASE 517AA ISSUE D



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

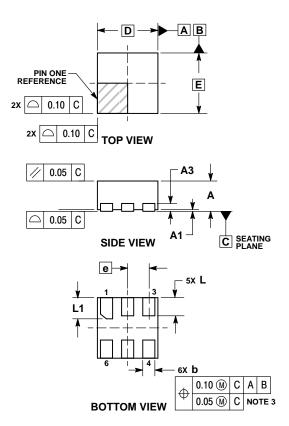
## **PACKAGE DIMENSIONS**

# UDFN6 1.45x1.0, 0.5P CASE 517AQ



#### PACKAGE DIMENSIONS

## UDFN6 1.0x1.0. 0.35P CASE 517BX **ISSUE O**

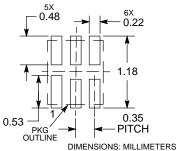


#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. PACKAGE DIMENSIONS EXCLUSIVE OF
- BURRS AND MOLD FLASH.

	MILLIMETERS							
DIM	MIN	MAX						
Α	0.45	0.55						
A1	0.00	0.05						
A3	0.13 REF							
b	0.12	0.22						
D	1.00 BSC							
E	1.00 BSC							
е	0.35 BSC							
L	0.25	0.35						
11	0.30	0.40						

#### RECOMMENDED **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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